

UFS540

NPN SILICON TRANSISTOR

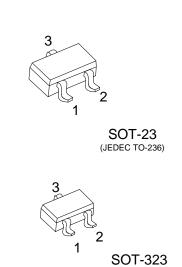
NPN 9GHz WIDEBAND TRANSISTOR

DESCRIPTION

The UTC **UFS540** are NPN silicon planar transistor, It is intended for RF wideband amplifier applications such as satellite TV systems and RF portable communication equipment with signal frequencies up to 2 GHz.

FEATURES

- * High power gain
- * Low noise figure
- * High transition frequency
- * Gold metallization ensures excellent reliability



ORDERING INFORMATION

Ordering Number		Dealiana	Pin Assignment			Deeking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UFS540L-AE3-R	UFS540G-AE3-R	SOT-23	В	ш	С	Tape Reel	
UFS540L-AL3-R	UFS540G-AL3-R	SOT-323	SOT-323 B E		С	Tape Reel	
Note: Pin Assignment: B: Base E: Emitter C: Collector							

UFS540G-AE3-R	
(1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) AE3: SOT-23, AL3: SOT-323
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		BV _{CBO}	20	V	
Collector-emitter voltage		BV _{CEO}	14	V	
Emitter-Base Voltage		BV _{EBO}	2.5	V	
Collector Current		lc	120	mA	
Collector Dissipation	SOT-23		250	mW	
	SOT-323	Pc	200	mW	
Junction Temperature		ΤJ	+150	°C	
Storage Temperature		T _{STG}	-50 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	ВV _{сво}	Open Emitter			20	V
Collector-Emitter Breakdown Voltage	BV _{CEO}	R _{BE} =0			14	V
Emitter-Base Breakdown Voltage	BV_{EBO}	Open Collector			2.5	V
DC Collector Current	lc				120	mA
Collector Cut-off Current	I _{CBO}	I _C =40mA, V _{CE} =8V			50	nA
DC Current Gain	h _{FE}	I _C =40mA, V _{CE} =8V	60	120	250	
Emitter Capacitance	Ce	I _C =i _C =0, V _{EB} =0.5V, f=1MHz		2.8		pF
Collector Capacitance	Cc	$I_E=i_e=0$, $V_{CB}=8V$, f=1MHz		3.4		pF
Feedback Capacitance	Cre	I _C =0, V _{CB} =8V, f=1MHz		2.4		pF
Transition Frequency	f⊤	I_{C} =40mA, V _{CE} =8V, f=1GHz, T _A =25°C		9		GHz



TYPICAL CHARACTERISTICS

25

50

75

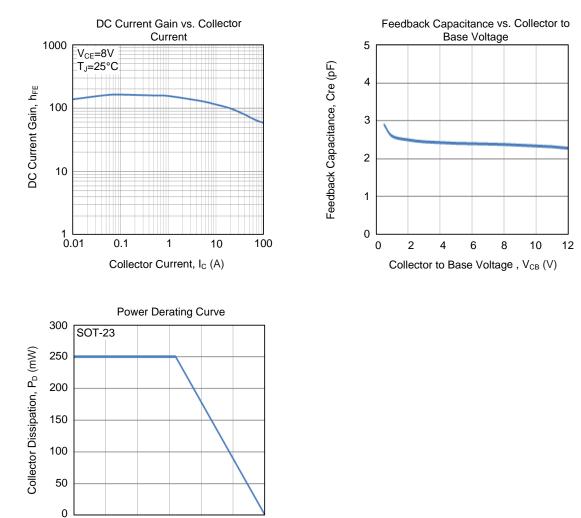
Junction Temperature, T_J (°C)

100

125

150

0



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